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Publications:

1. M Venkatesh, M Suguna, NB Balamurugan, Subthreshold Performance Analysis of Germanium Source Dual Halo Dual Dielectric Triple Material Surrounding Gate Tunnel Field Effect Transistor for Ultra Low Power Applications, Journal of Electronic Materials 48 (10), 6724-6734
2. S Manikandan, NB Balamurugan, TSA Samuel Impact of uniform and non-uniform doping variations for ultrathin body junctionless FinFETs, Materials Science in Semiconductor Processing 104, 104653
3. K Sowmya, NB Balamurugan, " Modeling and simulation of dual-material-gate AlGa_N/Ga_N high-electron-mobility transistor using finite difference method January 2019 International Journal of Numerical Modelling Electronic Networks Devices and Fields 32(1) DOI: 10.1002/jnm.2546
4. Dharshana, NB Balamurugan, TS Samuel, Journal of Nano Research, 2019, 57, 68-76, "An Analytical Modeling and Simulation of Surrounding Gate TFET with an Impact of Dual Material Gate and Stacked Oxide for Low Power Applications"
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8. G.Lakshmi Priya, N.B.Balamurugan, " New Dual Material Double Gate Junctionless Tunnel FET: Subthreshold Modeling and Simulation", International Journal of Electronics and Communications (2018) <https://doi.org/10.1016/j.aeue.2018.11.037>

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11. G.Lakshmi Priya, N.B.Balamurugan, "Subthreshold Modeling of Triple Material Gate-All-Around Junctionless Tunnel FET with Germanium and High-K Gate Dielectric Material", Journal of Microelectronics, Electronic Components and Materials Vol. 48, No. 1(2018), 53 – 61
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